

To: Radiation Physics and Chemistry Editorial Board
Subject: Article Submit

Dear Editors,

Enclosed with this letter you will find the electronic submission of manuscript entitled “Microwave induced transformation of defect in SiC and GaAs” O. Olikh and P. Lytvyn.

This is an original paper which has not been simultaneously submitted as a whole or in part anywhere else. No conflict of interest exists in the submission of this manuscript.

It is well known that defects are crucial for the semiconductor structure performance. As a result, the methods aimed at modifying the system of defects are very important for practical applications. The influence of certain factors, for example, radiation, has been studied quite well. At the same time, new agents begin to attract more attention, such as ultrasound loading or microwave treatment (MWT). The present manuscript describes MWT impact on the parameters of deep centers located in the near surface region of n -6H-SiC and n -GaAs single crystals, as well as on GaAs epitaxial structures. We believe that such way of defect modification would be of interest to the readers.

We would very much appreciate if you would consider the manuscript for publication in the *Radiation Physics and Chemistry*.

Sincerely yours,
Oleg Olikh and Petro Lytvyn
Taras Shevchenko National University of Kyiv
V. Lashkaryov Institute of Semiconductor Physics of NAS of Ukraine
E-mail: olegolikh@knu.ua